

Welcome to E-XFL.COM

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

ĿХF

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	252
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1afs1500-fgg676

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Device Architecture

Timing Characteristics

Table 2-1 • Combinatorial Cell Propagation DelaysCommercial Temperature Range Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	-2	-1	Std.	Units
INV	Y = !A	t _{PD}	0.40	0.46	0.54	ns
AND2	$Y = A \cdot B$	t _{PD}	0.47	0.54	0.63	ns
NAND2	$Y = !(A \cdot B)$	t _{PD}	0.47	0.54	0.63	ns
OR2	Y = A + B	t _{PD}	0.49	0.55	0.65	ns
NOR2	Y = !(A + B)	t _{PD}	0.49	0.55	0.65	ns
XOR2	Y = A ⊕ B	t _{PD}	0.74	0.84	0.99	ns
MAJ3	Y = MAJ(A, B, C)	t _{PD}	0.70	0.79	0.93	ns
XOR3	$Y = A \oplus B \oplus C$	t _{PD}	0.87	1.00	1.17	ns
MUX2	Y = A !S + B S	t _{PD}	0.51	0.58	0.68	ns
AND3	$Y = A \cdot B \cdot C$	t _{PD}	0.56	0.64	0.75	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

Sample VersaTile Specifications—Sequential Module

The Fusion library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library (Figure 2-5). For more details, refer to the *IGLOO*, *ProASIC3*, *SmartFusion and Fusion Macro Library Guide*.



Figure 2-5 • Sample of Sequential Cells



RC Oscillator

The RC oscillator is an on-chip free-running clock source generating a 100 MHz clock. It can be used as a source clock for both on-chip and off-chip resources. When used in conjunction with the Fusion PLL and CCC circuits, the RC oscillator clock source can be used to generate clocks of varying frequency and phase.

The Fusion RC oscillator is very accurate at $\pm 1\%$ over commercial temperature ranges and and $\pm 3\%$ over industrial temperature ranges. It is an automated clock, requiring no setup or configuration by the user. It requires only that the power and GNDOSC pins be connected; no external components are required. The RC oscillator can be used to drive either a PLL or another internal signal.

RC Oscillator Characteristics

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
	Operating Frequency			100		MHz
Fac	Accuracy	Temperature: 0°C to 85°C Voltage: 3.3 V ± 5%		1		%
		Temperature: -40° C to 125° C Voltage: 3.3 V ± 5%		3		%
	Output Jitter	Period Jitter (at 5 k cycles)		100		ps
NO		Cycle–Cycle Jitter (at 5 k cycles)		100		ps
		Period Jitter (at 5 k cycles) with 1 KHz / 300 mV peak-to-peak noise on power supply		150		ps
		Cycle–Cycle Jitter (at 5 k cycles) with 1 KHz / 300 mV peak-to-peak noise on power supply		150		ps
	Output Duty Cycle			50		%
IDYNRC	Operating Current			1		mA

Table 2-9 • Electrical Characteristics of RC Oscillator

Voltage Regulator and Power System Monitor (VRPSM)

The VRPSM macro controls the power-up state of the FPGA. The power-up bar (PUB) pin can turn on the voltage regulator when set to 0. TRST can enable the voltage regulator when deasserted, allowing the FPGA to power-up when user want access to JTAG ports. The inputs VRINITSTATE and RTCPSMMATCH come from the flash bits and RTC, and can also power up the FPGA.



Note: *Signals are hardwired internally and do not exist in the macro core.

Figure 2-30 • VRPSM Macro

Table 2-17 • VRPSM Signal Descriptions

Signal Name	Width	Direction	Function
VRPU	1	In	Voltage Regulator Power-Up
			0 – Voltage regulator disabled. PUB must be floated or pulled up, and the TRST pin must be grounded to disable the voltage regulator.
			1 – Voltage regulator enabled
VRINITSTATE	1	In	Voltage Regulator Initial State
			Defines the voltage Regulator status upon power-up of the 3.3 V. The signal is configured by Libero SoC when the VRPSM macro is generated.
			Tie off to 1 – Voltage regulator enables when 3.3 V is powered.
			Tie off to 0 – Voltage regulator disables when 3.3 V is powered.
RTCPSMMATCH	1	In	RTC Power System Management Match
			Connect from RTCPSMATCH signal from RTC in AB
			0 transition to 1 turns on the voltage regulator
PUB	1	In	External pin, built-in weak pull-up
			Power-Up Bar
			0 – Enables voltage regulator at all times
TRST*	1	In	External pin, JTAG Test Reset
			1 – Enables voltage regulator at all times
FPGAGOOD	1	Out	Indicator that the FPGA is powered and functional
			No need to connect if it is not used.
			1 – Indicates that the FPGA is powered up and functional.
			0 – Not possible to read by FPGA since it has already powered off.
PUCORE	1	Out	Power-Up Core
			Inverted signal of PUB. No need to connect if it is not used.
VREN*	1	Out	Voltage Regulator Enable
			Connected to 1.5 V voltage regulator in Fusion device internally.
			0 – Voltage regulator disables
			1 – Voltage regulator enables
Note: *Signals a	re hard	wired interr	ally and do not exist in the macro core.

Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven
 onto the RD bus in the same clock cycle following RA and REN valid. The read address is
 registered on the read port clock active edge, and data appears at RD after the RAM access time.
 Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from the address to the data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is High. The setup times of the write address, write enables, and write data are minimal with respect to the write clock. Write and read transfers are described with timing requirements in the "SRAM Characteristics" section on page 2-63 and the "FIFO Characteristics" section on page 2-72.

RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism (refer to the "JTAG IEEE 1532" section on page 2-229 and the *Fusion SRAM/FIFO Blocks* application note). The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

Temperature Monitor

The final pin in the Analog Quad is the Analog Temperature (AT) pin. The AT pin is used to implement an accurate temperature monitor in conjunction with an external diode-connected bipolar transistor (Figure 2-76). For improved temperature measurement accuracy, it is important to use the ATRTN pin for the return path of the current sourced by the AT pin. Each ATRTN pin is shared between two adjacent Analog Quads. Additionally, if not used for temperature monitoring, the AT pin can provide functionality similar to that of the AV pad. However, in this mode only positive voltages can be applied to the AT pin, and only two prescaler factors are available (16 V and 4 V ranges—refer to Table 2-57 on page 2-130).



Figure 2-76 • Temperature Monitor Quad



Fusion uses a remote diode as a temperature sensor. The Fusion Temperature Monitor uses a differential input; the AT pin and ATRTN (AT Return) pin are the differential inputs to the Temperature Monitor. There is one Temperature Monitor in each Quad. A simplified block diagram is shown in Figure 2-77.



Figure 2-77 • Block Diagram for Temperature Monitor Circuit

The Fusion approach to measuring temperature is forcing two different currents through the diode with a ratio of 10:1. The switch that controls the different currents is controlled by the Temperature Monitor Strobe signal, TMSTB. Setting TMSTB to '1' will initiate a Temperature reading. The TMSTB should remain '1' until the ADC finishes sampling the voltage from the Temperature Monitor. The minimum sample time for the Temperature Monitor cannot be less than the minimum strobe high time minus the setup time. Figure 2-78 shows the timing diagram.





Note: When the IEEE 1149.1 Boundary Scan EXTEST instruction is executed, the AG pad drive strength ceases and becomes a 1 µA sink into the Fusion device.



Device Architecture

Refer to Table 2-46 on page 2-109 and the "Acquisition Time or Sample Time Control" section on page 2-107

$$t_{sample} = (2 + STC) \times t_{ADCCLK}$$

EQ 20

STC: Sample Time Control value (0–255)

t_{SAMPLE} is the sample time

Table 2-46 • STC Bits Function

Name	Bits	Function
STC	[7:0]	Sample time control

Sample time is computed based on the period of ADCCLK.

Distribution Phase

The second phase is called the distribution phase. During distribution phase, the ADC computes the equivalent digital value from the value stored in the input capacitor. In this phase, the output signal SAMPLE goes back to '0', indicating the sample is completed; but the BUSY signal remains '1', indicating the ADC is still busy for distribution. The distribution time depends strictly on the number of bits. If the ADC is configured as a 10-bit ADC, then 10 ADCCLK cycles are needed. EQ 8 describes the distribution time.

$$t_{distrib} = N \times t_{ADCCLK}$$

EQ 21

N: Number of bits

Post-Calibration Phase

The last phase is the post-calibration phase. This is an optional phase. The post-calibration phase takes two ADCCLK cycles. The output BUSY signal will remain '1' until the post-calibration phase is completed. If the post-calibration phase is skipped, then the BUSY signal goes to '0' after distribution phase. As soon as BUSY signal goes to '0', the DATAVALID signal goes to '1', indicating the digital result is available on the RESULT output signals. DATAVAILD will remain '1' until the next ADCSTART is asserted. Microsemi recommends enabling post-calibration to compensate for drift and temperature-dependent effects. This ensures that the ADC remains consistent over time and with temperature. The post-calibration phase is enabled by bit 3 of the Mode register. EQ 9 describes the post-calibration time.

$$t_{post-cal} = MODE[3] \times (2 \times t_{ADCCLK})$$

EQ 22

EQ 23

MODE[3]: Bit 3 of the Mode register, described in Table 2-41 on page 2-106.

The calculation for the conversion time for the ADC is summarized in EQ 23.

 $t_{conv} = t_{sync_read} + t_{sample} + t_{distrib} + t_{post-cal} + t_{sync_write}$

t_{conv}: conversion time

 t_{sync_read} : maximum time for a signal to synchronize with SYSCLK. For calculation purposes, the worst case is a period of SYSCLK, t_{SYSCLK} .

t_{sample}: Sample time

t_{distrib}: Distribution time

tpost-cal: Post-calibration time

 t_{sync_write} : Maximum time for a signal to synchronize with SYSCLK. For calculation purposes, the worst case is a period of SYSCLK, t_{SYSCLK} .

Table 2-50 • ADC Characteristics in Direct Input ModeCommercial Temperature Range Conditions, TJ = 85°C (unless noted otherwise),Typical: VCC33A = 3.3 V, VCC = 1.5 V

Parameter	Description	Condition	Min.	Тур.	Max.	Units
Direct Input	using Analog Pad AV, AC, A	Г				
VINADC	Input Voltage (Direct Input)	Refer to Table 3-2 on page 3-3				
CINADC	Input Capacitance	Channel not selected		7		pF
		Channel selected but not sampling		8		pF
		Channel selected and sampling		18		pF
ZINADC	Input Impedance	8-bit mode		2		kΩ
		10-bit mode		2		kΩ
		12-bit mode		2		kΩ
Analog Refe	erence Voltage VAREF					
VAREF	Accuracy	T _J = 25°C	2.537	2.56	2.583	V
	Temperature Drift of Internal Reference			65		ppm / °C
	External Reference		2.527		VCC33A + 0.05	V
ADC Accura	acy (using external reference) 1,2				
DC Accurac	y					
TUE	Total Unadjusted Error	8-bit mode		0.29		LSB
		10-bit mode		0.7	72	LSB
		12-bit mode		1.	8	LSB
INL	Integral Non-Linearity	8-bit mode		0.20	0.25	LSB
		10-bit mode		0.32	0.43	LSB
		12-bit mode		1.71	1.80	LSB
DNL	Differential Non-Linearity (no missing code)	8-bit mode		0.20	0.24	LSB
		10-bit mode		0.60	0.65	LSB
		12-bit mode		2.40	2.48	LSB
	Offset Error	8-bit mode		0.01	0.17	LSB
		10-bit mode		0.05	0.20	LSB
		12-bit mode		0.20	0.40	LSB
	Gain Error	8-bit mode		0.0004	0.003	LSB
		10-bit mode		0.002	0.011	LSB
		12-bit mode		0.007	0.044	LSB
	Gain Error (with internal reference)	All modes		2		% FSR

Notes:

1. Accuracy of the external reference is 2.56 V \pm 4.6 mV.

2. Data is based on characterization.

3. The sample rate is time-shared among active analog inputs.

Analog Configuration MUX

The ACM is the interface between the FPGA, the Analog Block configurations, and the real-time counter. Microsemi Libero SoC will generate IP that will load and configure the Analog Block via the ACM. However, users are not limited to using the Libero SoC IP. This section provides a detailed description of the ACM's register map, truth tables for proper configuration of the Analog Block and RTC, as well as timing waveforms so users can access and control the ACM directly from their designs.

The Analog Block contains four 8-bit latches per Analog Quad that are initialized through the ACM. These latches act as configuration bits for Analog Quads. The ACM block runs from the core voltage supply (1.5 V).

Access to the ACM is achieved via 8-bit address and data busses with enables. The pin list is provided in Table 2-36 on page 2-78. The ACM clock speed is limited to a maximum of 10 MHz, more than sufficient to handle the low-bandwidth requirements of configuring the Analog Block and the RTC (sub-block of the Analog Block).

Table 2-54 decodes the ACM address space and maps it to the corresponding Analog Quad and configuration byte for that quad.

ACMADDR [7:0] in Decimal	Name	Description	Associated Peripheral
0	-	_	Analog Quad
1	AQ0	Byte 0	Analog Quad
2	AQ0	Byte 1	Analog Quad
3	AQ0	Byte 2	Analog Quad
4	AQ0	Byte 3	Analog Quad
5	AQ1	Byte 0	Analog Quad
			Analog Quad
	· .	· · ·	
36	AQ8	Byte 3	Analog Quad
37	AQ9	Byte 0	Analog Quad
38	AQ9	Byte 1	Analog Quad
39	AQ9	Byte 2	Analog Quad
40	AQ9	Byte 3	Analog Quad
41		Undefined	Analog Quad
		Undefined	Analog Quad
	· · ·		
63		Undefined	RTC
64	COUNTER0	Counter bits 7:0	RTC
65	COUNTER1	Counter bits 15:8	RTC
66	COUNTER2	Counter bits 23:16	RTC
67	COUNTER3	Counter bits 31:24	RTC
68	COUNTER4	Counter bits 39:32	RTC
72	MATCHREG0	Match register bits 7:0	RTC

Table 2-54 • ACM Address Decode Table for Analog Quad



Detailed I/O DC Characteristics

Table 2-95 • Input Capacitance

Symbol	Definition	Conditions	Min.	Max.	Units
C _{IN}	Input capacitance	VIN = 0, f = 1.0 MHz		8	pF
C _{INCLK}	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz		8	pF

Table 2-96 • I/O Output Buffer Maximum Resistances ¹

Drive Strength	R _{PULL-DOWN} (ohms) ²	R _{PULL-UP} (ohms) ³
4 mA	100	300
8 mA	50	150
12 mA	25	75
16 mA	17	50
24 mA	11	33
4 mA	100	200
8 mA	50	100
12 mA	25	50
16 mA	20	40
24 mA	11	22
2 mA	200	225
4 mA	100	112
6 mA	50	56
8 mA	50	56
12 mA	20	22
16 mA	20	22
2 mA	200	224
4 mA	100	112
6 mA	67	75
8 mA	33	37
12 mA	33	37
Per PCI/PCI-X specification	25	75
20 mA	11	-
20 mA	14	-
35 mA	12	-
33 mA	15	_
	Drive Strength 4 mA 8 mA 12 mA 16 mA 24 mA 4 mA 8 mA 12 mA 16 mA 24 mA 4 mA 8 mA 12 mA 16 mA 24 mA 6 mA 8 mA 112 mA 16 mA 2 mA 4 mA 6 mA 8 mA 12 mA 16 mA 8 mA 12 mA 12 mA 13 mA Per PCI/PCI-X specification 20 mA 35 mA 33 mA	Drive Strength "PULL-DOWN (ohms) 2" 4 mA 100 8 mA 50 12 mA 25 16 mA 17 24 mA 11 4 mA 100 8 mA 50 12 mA 25 16 mA 11 4 mA 100 8 mA 50 12 mA 25 16 mA 20 24 mA 11 2 mA 200 4 mA 100 6 mA 50 12 mA 20 16 mA 20 2 mA 200 4 mA 100 6 mA 50 12 mA 20 2 mA 200 4 mA 100 6 mA 67 8 mA 33 12 mA 33 Per PCI/PCI-X specification 25 20 mA 11 20 mA 14 <

Notes:

 These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCC, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: http://www.microsemi.com/soc/techdocs/models/ibis.html.

2. R_(PULL-DOWN-MAX) = VOLspec / I_{OLspec}

3. R_(PULL-UP-MAX) = (VCCImax – VOHspec) / IOHspec



Device Architecture

Table 2-98 • I/O Short Currents IOSH/IOSL (continued)

	Drive Strength	IOSH (mA)*	IOSL (mA)*
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109
Applicable to Standard I/O Banks			
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
1.5 V LVCMOS	2 mA	13	16

Note: $^{*}T_{J} = 100^{\circ}C$

The length of time an I/O can withstand IOSH/IOSL events depends on the junction temperature. The reliability data below is based on a 3.3 V, 36 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.



Device Architecture

HSTL Class I

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). Fusion devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

HSTL Class I		VIL	VIH		VOL	VOH	IOL	юн	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
8 mA	-0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8	39	32	10	10

Table 2-150 • Minimum and Maximum DC Input and Output Levels

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.



Figure 2-128 • AC Loading

Table 2-151 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)	
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20	

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics

Table 2-152 • HSTL Class I

Commercial Temperature Range Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V, VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.66	3.18	0.04	2.12	0.43	3.24	3.14			5.47	5.38	ns
-1	0.56	2.70	0.04	1.81	0.36	2.75	2.67			4.66	4.58	ns
-2	0.49	2.37	0.03	1.59	0.32	2.42	2.35			4.09	4.02	ns

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). Fusion devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-153	Minimum	and Maximum	DC Inpu	t and Out	out Levels
1 4 10 1 1 0 0					041 - 01010

HSTL Class II		VIL	VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
15 mA ³	-0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15	55	66	10	10

Note:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Output drive strength is below JEDEC specification.



Figure 2-129 • AC Loading

Table 2-154 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics

Table 2-155 • HSTL Class II

```
Commercial Temperature Range Conditions: T_J = 70^{\circ}C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V, VREF = 0.75 V
```

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.66	3.02	0.04	2.12	0.43	3.08	2.71			5.32	4.95	ns
-1	0.56	2.57	0.04	1.81	0.36	2.62	2.31			4.52	4.21	ns
-2	0.49	2.26	0.03	1.59	0.32	2.30	2.03			3.97	3.70	ns

SSTL3 Class II

Stub-Speed Terminated Logic for 3.3 V memory bus standard (JESD8-8). Fusion devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

SSTL3 Class II		VIL	VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
21 mA	-0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21	109	103	10	10

Table 2-165 • Minimum and Maximum DC Input and Output Levels

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.



Figure 2-133 • AC Loading

Table 2-166 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.5	1.5	1.485	30

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics

Table 2-167 • SSTL3- Class II Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V, VREF = 1.5 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.66	2.07	0.04	1.25	0.43	2.10	1.67			4.34	3.91	ns
-1	0.56	1.76	0.04	1.06	0.36	1.79	1.42			3.69	3.32	ns
-2	0.49	1.54	0.03	0.93	0.32	1.57	1.25			3.24	2.92	ns



LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-136. The building blocks of the LVPECL transmitter–receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.



EINUNA 2 426 . IVDECI	Circuit Disarom and Deard La	
FIGHTE Z=1.30 • 1 VPFL.1	CITCUU DIAOFAM AND BOAFO-LE	vei impiementation
1 IYUIC 2-130 ° LVFLOL	Circuit Diagram and Doard-Le	

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-171 • Minimum and Maximum DC Input and Output Levels

Table 2-172 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)		
1.64	1.94	Cross point	_		

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics

Table 2-173 • LVPECL

Commercial Temperature Range Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Pro I/Os

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	Units
Std.	0.66	2.14	0.04	1.63	ns
-1	0.56	1.82	0.04	1.39	ns
-2	0.49	1.60	0.03	1.22	ns



DDR Module Specifications

Input DDR Module



Figure 2-142 • Input DDR Timing Model

Table 2-179 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t _{DDRICLKQ1}	Clock-to-Out Out_QR	B, D
t _{DDRICLKQ2}	Clock-to-Out Out_QF	B, E
t _{DDRISUD}	Data Setup Time of DDR Input	А, В
t _{DDRIHD}	Data Hold Time of DDR Input	А, В
t _{DDRICLR2Q1}	Clear-to-Out Out_QR	C, D
t _{DDRICLR2Q2}	Clear-to-Out Out_QF	C, E
t _{DDRIREMCLR}	Clear Removal	С, В
t _{DDRIRECCLR}	Clear Recovery	С, В

Power Consumption

Table 3-18 • Power Consumption

Parameter	Description	Condition	Min.	Typical	Max.	Units
Crystal Oscillator						•
ISTBXTAL	Standby Current of Crystal Oscillator			10		μΑ
IDYNXTAL	Operating Current	RC		0.6		mA
		0.032-0.2		0.19		mA
		0.2–2.0		0.6		mA
		2.0–20.0		0.6		mA
RC Oscillator						•
IDYNRC	Operating Current			1		mA
ACM						•
	Operating Current (fixed clock)			200		µA/MHz
	Operating Current (user clock)			30		μΑ
NVM System						
	NVM Array Operating Power	Idle		795		μA
		Read operation		See Table 3-15 on page 3-23.		See Table 3-15 on page 3-23.
		Erase		900		μA
		Write		900		μA
PNVMCTRL	NVM Controller Operating Power			20		µW/MHz



Package Pin Assignments

QN180			QN180			
Pin Number	AFS090 Function	AFS250 Function	Pin Number	AFS090 Function	AFS250 Function	
A1	GNDQ	GNDQ	A37	VPUMP	VPUMP	
A2	VCCIB3	VCCIB3	A38	TDI	TDI	
A3	GAB2/IO52NDB3V0	IO74NDB3V0	A39	TDO	TDO	
A4	GFA2/IO51NDB3V0	IO71NDB3V0	A40	VJTAG	VJTAG	
A5	GFC2/IO50NDB3V0	IO69NPB3V0	A41	GDB1/IO39PPB1V0	GDA1/IO54PPB1V0	
A6	VCCIB3	VCCIB3	A42	GDC1/IO38PDB1V0	GDB1/IO53PDB1V0	
A7	GFA1/IO47PPB3V0	GFB1/IO67PPB3V0	A43	VCC	VCC	
A8	GEB0/IO45NDB3V0	NC	A44	GCB0/IO35NPB1V0	GCB0/IO48NPB1V0	
A9	XTAL1	XTAL1	A45	GCC1/IO34PDB1V0	GCC1/IO47PDB1V0	
A10	GNDOSC	GNDOSC	A46	VCCIB1	VCCIB1	
A11	GEC2/IO43PPB3V0	GEA1/IO61PPB3V0	A47	GBC2/IO32PPB1V0	GBB2/IO41PPB1V0	
A12	IO43NPB3V0	GEA0/IO61NPB3V0	A48	VCCIB1	VCCIB1	
A13	NC	VCCIB3	A49	NC	NC	
A14	GNDNVM	GNDNVM	A50	GBA0/IO29RSB0V0	GBB1/IO37RSB0V0	
A15	PCAP	PCAP	A51	VCCIB0	VCCIB0	
A16	VCC33PMP	VCC33PMP	A52	GBB0/IO27RSB0V0	GBC0/IO34RSB0V0	
A17	NC	NC	A53	GBC1/IO26RSB0V0	IO33RSB0V0	
A18	AV0	AV0	A54	IO24RSB0V0	IO29RSB0V0	
A19	AG0	AG0	A55	IO21RSB0V0	IO26RSB0V0	
A20	ATRTN0	ATRTN0	A56	VCCIB0	VCCIB0	
A21	AG1	AG1	A57	IO15RSB0V0	IO21RSB0V0	
A22	AC1	AC1	A58	IO10RSB0V0	IO13RSB0V0	
A23	AV2	AV2	A59	IO07RSB0V0	IO10RSB0V0	
A24	AT2	AT2	A60	GAC0/IO04RSB0V0	IO06RSB0V0	
A25	AT3	AT3	A61	GAB1/IO03RSB0V0	GAC1/IO05RSB0V0	
A26	AC3	AC3	A62	VCC	VCC	
A27	AV4	AV4	A63	GAA1/IO01RSB0V0	GAB0/IO02RSB0V0	
A28	AC4	AC4	A64	NC	NC	
A29	AT4	AT4	B1	VCOMPLA	VCOMPLA	
A30	NC	AG5	B2	GAA2/IO52PDB3V0	GAC2/IO74PDB3V0	
A31	NC	AV5	B3	GAC2/IO51PDB3V0	GFA2/IO71PDB3V0	
A32	ADCGNDREF	ADCGNDREF	B4	GFB2/IO50PDB3V0	GFB2/IO70PSB3V0	
A33	VCC33A	VCC33A	B5	VCC	VCC	
A34	GNDA	GNDA	B6	GFC0/IO49NDB3V0	GFC0/IO68NDB3V0	
A35	PTBASE	PTBASE	B7	GEB1/IO45PDB3V0	NC	
A36	VCCNVM	VCCNVM	B8	VCCOSC	VCCOSC	



Datasheet Information

Revision	Changes	Page
Advance v1.0 (January 2008)	All Timing Characteristics tables were updated. For the Differential I/O Standards, the Standard I/O support tables are new.	N/A
	Table 2-3 • Array Coordinates was updated to change the max x and y values	2-9
	Table 2-12 • Fusion CCC/PLL Specification was updated.	2-31
	A note was added to Table 2-16 · RTC ACM Memory Map.	2-37
	A reference to the Peripheral's User's Guide was added to the "Voltage Regulator Power Supply Monitor (VRPSM)" section.	2-42
	In Table 2-25 • Flash Memory Block Timing, the commercial conditions were updated.	2-55
	In Table 2-26 • FlashROM Access Time, the commercial conditions were missing and have been added below the title of the table.	2-58
	In Table 2-36 • Analog Block Pin Description, the function description was updated for the ADCRESET.	2-82
	In the "Voltage Monitor" section, the following sentence originally had \pm 10% and it was changed to +10%.	2-86
	The Analog Quad inputs are tolerant up to 12 V + 10%.	
	In addition, this statement was deleted from the datasheet:	
	Each I/O will draw power when connected to power (3 mA at 3 V).	0.00
	The "Terminology" section is new.	2-88
	The "Current Monitor" section was significantly updated. Figure 2-72 • Timing Diagram for Current Monitor Strobe to Figure 2-74 • Negative Current Monitor and Table 2-37 • Recommended Resistor for Different Current Range Measurement are new.	2-90
	The "ADC Description" section was updated to add the "Terminology" section.	2-93
	In the "Gate Driver" section, 25 mA was changed to 20 mA and 1.5 MHz was changed to 1.3 MHz. In addition, the following sentence was deleted: The maximum AG pad switching frequency is 1.25 MHz.	2-94
	The "Temperature Monitor" section was updated to rewrite most of the text and add Figure 2-78, Figure 2-79, and Table 2-38 • Temperature Data Format.	2-96
	In Table 2-38 • Temperature Data Format, the temperature K column was changed for 85°C from 538 to 358.	2-98
	In Table 2-45 • ADC Interface Timing, "Typical-Case" was changed to "Worst-Case."	2-110
	The "ADC Interface Timing" section is new.	2-110
	Table 2-46 • Analog Channel Specifications was updated.	2-118
	The "V _{CC15A} Analog Power Supply (1.5 V)" section was updated.	2-224
	The "V _{CCPLA/B} PLL Supply Voltage" section is new.	2-225
	In "V $_{\rm CCNVM}$ Flash Memory Block Power Supply (1.5 V)" section, supply was changed to supply input.	2-224
	The "V_{CCPLAVB} PLL Supply Voltage" pin description was updated to include the following statement:	2-225
	Actel recommends tying VCCPLX to VCC and using proper filtering circuits to decouple V_{CC} noise from PLL.	
	The "V _{COMPLA/B} Ground for West and East PLL" section was updated.	2-225



Datasheet Information

Revision	Changes	Page
Advance v0.5 (June 2006)	The low power modes of operation were updated and clarified.	
	The AFS1500 digital I/O count was updated in Table 1 • Fusion Family.	
	The AFS1500 digital I/O count was updated in the "Package I/Os: Single-/Double- Ended (Analog)" table.	
	The "Voltage Regulator Power Supply Monitor (VRPSM)" was updated.	2-36
	Figure 2-45 • FlashROM Timing Diagram was updated.	2-53
	The "256-Pin FBGA" table for the AFS1500 is new.	3-12
Advance v0.4 (April 2006)	The G was moved in the "Product Ordering Codes" section.	III
Advance v0.3 (April 2006)	The "Features and Benefits" section was updated.	I
	The "Fusion Family" table was updated.	I
	The "Package I/Os: Single-/Double-Ended (Analog)" table was updated.	П
	The "Product Ordering Codes" table was updated.	Ш
	The "Temperature Grade Offerings" table was updated.	IV
	The "General Description" section was updated to include ARM information.	1-1
	Figure 2-46 • FlashROM Timing Diagram was updated.	2-58
	The "FlashROM" section was updated.	2-57
	The "RESET" section was updated.	2-61
	The "RESET" section was updated.	2-64
	Figure 2-27 · Real-Time Counter System was updated.	2-35
	Table 2-19 • Flash Memory Block Pin Names was updated.	2-43
	Figure 2-33 • Flash Memory Block Diagram was updated to include AUX block information.	2-45
	Figure 2-34 • Flash Memory Block Organization was updated to include AUX block information.	2-46
	The note in the "Program Operation" section was updated.	2-48
	Figure 2-76 • Gate Driver Example was updated.	2-95
	The "Analog Quad ACM Description" section was updated.	2-130
	Information about the maximum pad input frequency was added to the "Gate Driver" section.	2-94
	Figure 2-65 • Analog Block Macro was updated.	2-81
	Figure 2-65 • Analog Block Macro was updated.	2-81
	The "Analog Quad" section was updated.	2-84
	The "Voltage Monitor" section was updated.	2-86
	The "Direct Digital Input" section was updated.	2-89
	The "Current Monitor" section was updated.	2-90
	Information about the maximum pad input frequency was added to the "Gate Driver" section.	2-94